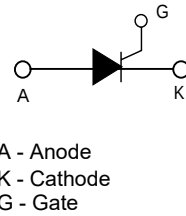
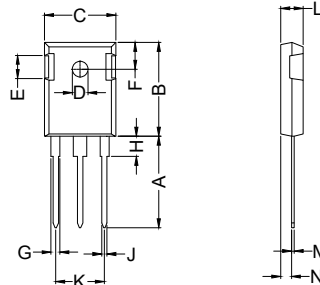


STOE50G12B2

High Efficiency Thyristor Discretes



Dimensions TO-247AD



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.620	0.640
ØD	3.15	3.65	0.124	0.144
E	4.32	5.49	0.170	0.216
F	5.40	6.30	0.213	0.248
G	1.65	2.18	0.065	0.086
H	3.80	4.50	0.150	0.177
J	1.00	1.40	0.039	0.055
K	10.80	11.10	0.425	0.437
L	4.70	5.30	0.185	0.209
M	0.40	0.80	0.016	0.031
N	1.50	2.49	0.059	0.098

	V_{RRM} V	V_{RSM} V
STOE50G12B2	1200	1300



Symbol	Test Conditions		Maximum Ratings	Unit
I_{TRMS} I_{TAVM}	$T_{VJ}=T_{VJM}$ $T_C=125^{\circ}C$; 180°sine		80 50	A
I_{TSM}	$T_{VJ}=45^{\circ}C$ $V_R=0$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	650 700	A
	$T_{VJ}=T_{VJM}$ $V_R=0$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	556 600	
I^2t	$T_{VJ}=45^{\circ}C$ $V_R=0$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	2120 2040	A^2s
	$T_{VJ}=T_{VJM}$ $V_R=0$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	1540 1480	
$(di/dt)_{cr}$	$T_{VJ}=T_{VJM}$ $f=50Hz$, $t_p=200\mu s$ $V_D=2/3V_{DRM}$ $I_G=0.3A$ $di_G/dt=0.3A/\mu s$	repetitive, $I_T=150A$	150	A/ μs
		non repetitive, $I_T=50A$	500	
$(dv/dt)_{cr}$	$T_{VJ}=T_{VJM}$; $R_{GK}=\infty$; method 1 (linear voltage rise)	$V_{DR}=2/3V_{DRM}$	1000	V/ μs
P_{GM}	$T_{VJ}=T_{VJM}$ $I_T=I_{TAVM}$	$t_p=30\mu s$ $t_p=300\mu s$	10 5	W
P_{GAV}			0.5	W
V_{RGM}			10	V
T_{VJ} T_{VJM} T_{stg}			-55...+150 150 -55...+150	$^{\circ}C$
M_d F_c	Mounting torque (M3) Mounting force with clip		0.8...1.2 20...120	Nm N
Weight	typical		6	g

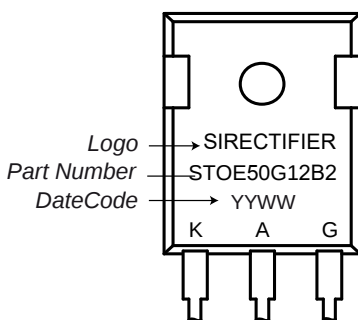
Sirectifier®

STOE50G12B2

High Efficiency Thyristor Discretes

Symbol	Test Conditions	Characteristic Values	Unit
I_R, I_D	$T_{VJ}=T_{VJM}; V_R=V_{RRM}; V_D=V_{DRM}$	3	mA
V_{TM}	$I_{TM}=50A; T_{VJ}=25^{\circ}C$	1.30	V
V_{TO}	For power-loss calculations only ($T_{VJ}=150^{\circ}C$)	0.88	V
r_T		7.7	m Ω
V_{GT}	$V_D=6V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	1.5 1.6	V
I_{GT}	$V_D=6V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$ $T_{VJ}=125^{\circ}C$	50 80 30	mA
V_{GD}	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	0.2	V
I_{GD}		3	mA
I_L	$T_{VJ}=25^{\circ}C; t_p=10\mu s;$ $I_G=0.3A; di_G/dt=0.3A/\mu s$	125	mA
I_H	$T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$	100	mA
t_{gd}	$T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM}$ $I_G=0.3A; di_G/dt=0.3A/\mu s$	2	μs
R_{thJC}	DC current	0.25	K/W
R_{thch}	DC current	0.25	K/W
a	Max. acceleration, 50 Hz	50	m/s ²

Product Marking



Features / Advantages:

- Thyristor for line frequency
- Glass passivated chip

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-247AD

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Standard applicable

- IEC191-1/4
- IEC747-1
- IEC747-6
- IEC68-2-...
- UL94-V0

ORDERING INFORMATION

Part Number	Package	Shipping	Marking Code
STOE50G12B2	TO-247AD	30pcs / Tube	STOE50G12B2

STOE50G12B2

High Efficiency Thyristor Discretes

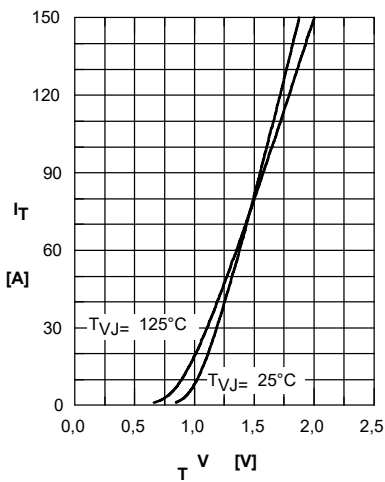


Fig. 1 Forward characteristics

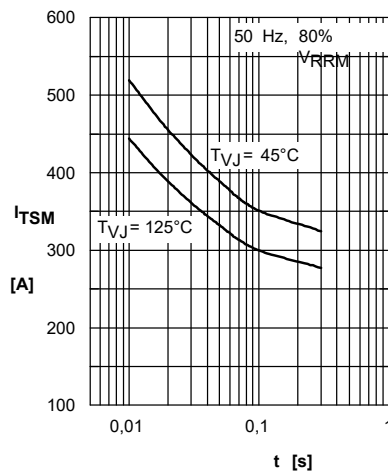


Fig. 2 Surge overload current
 I_{TSM} : crest value, t : duration

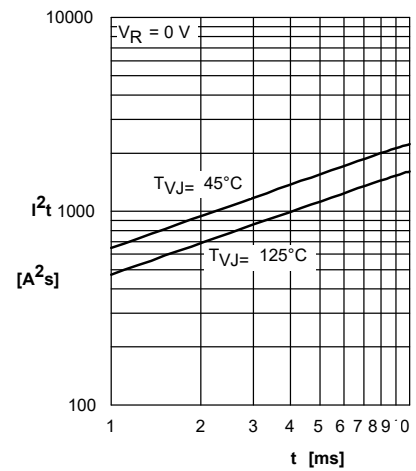


Fig. 3 I^2t versus time (1-10 s)

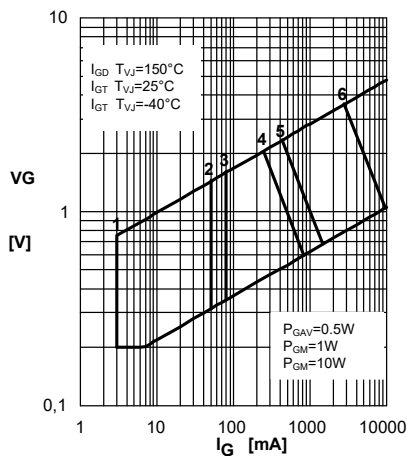


Fig. 4 Gate voltage & gate current

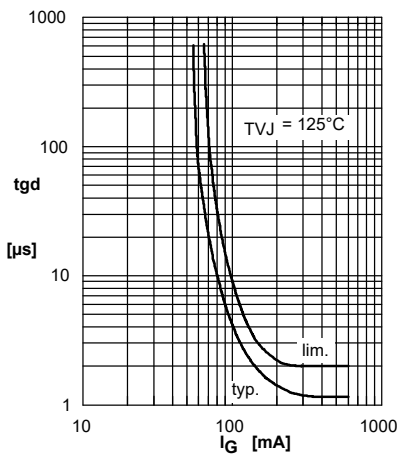


Fig. 5 Gate controlled delay time t_{gd}

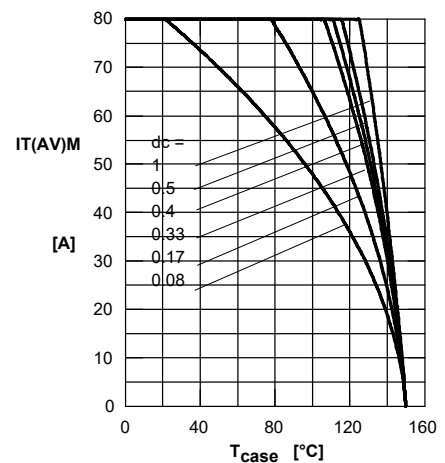


Fig. 6 Max. forward current at case temperature

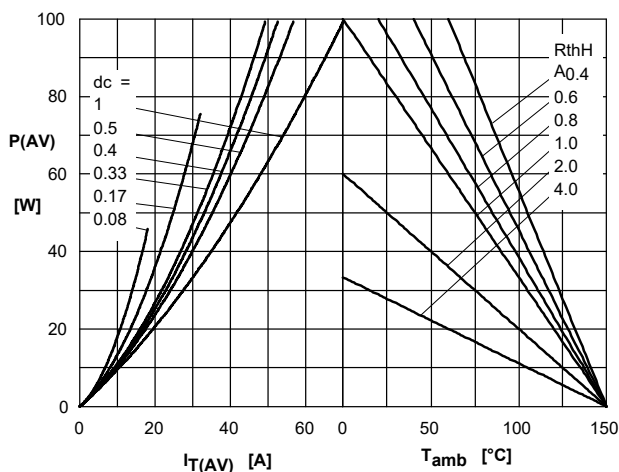


Fig. 7a Power dissipation versus direct output current

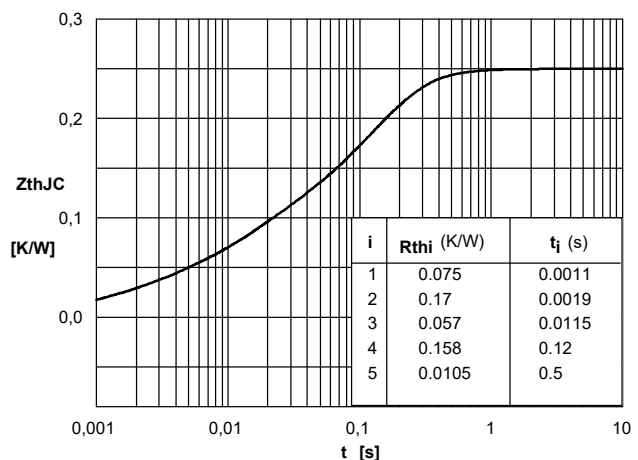


Fig. 7 Transient thermal impedance junction to case